

SANYO

No.2963

2SC4293

NPN Triple Diffused Planar Silicon Transistor
 Very High-Definition Color Display
 Horizontal Deflection Output Applications

Features

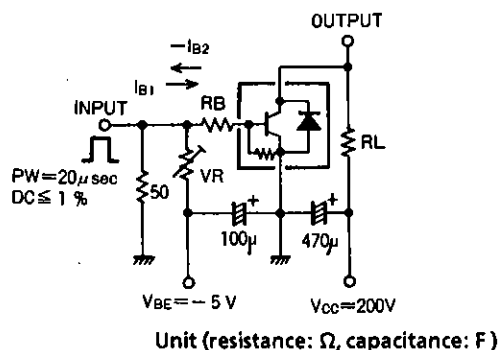
- High speed ($t_f = 300\text{ns}$ max)
- High breakdown voltage ($V_{CBO} = 1500\text{V}$)
- High reliability (adoption of HVP process)
- Adoption of MBIT process
- On-chip damper diode

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

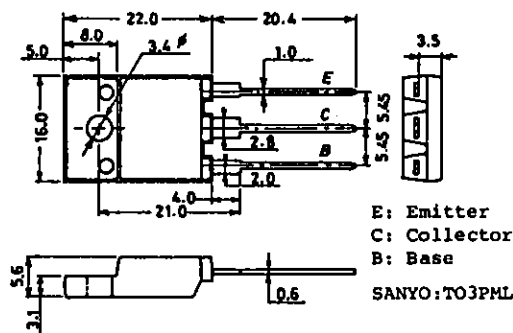
			unit
Collector to Base Voltage	V_{CBO}	1500	V
Collector to Emitter Voltage	V_{CEO}	800	V
Emitter to Base Voltage	V_{EBO}	7	V
Collector Current	I_C	5	A
Peak Collector Current	i_{cp}	16	A
Collector Dissipation	P_C	3.0	W
		50	W
		150	$^\circ\text{C}$
Junction Temperature	T_j		
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

 $T_c = 25^\circ\text{C}$ **Electrical Characteristics at $T_a = 25^\circ\text{C}$**

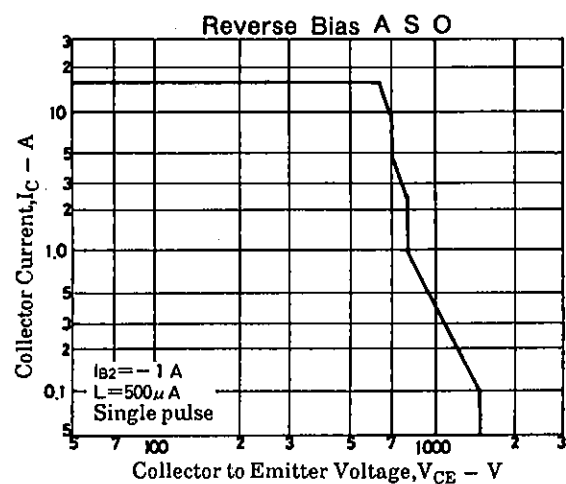
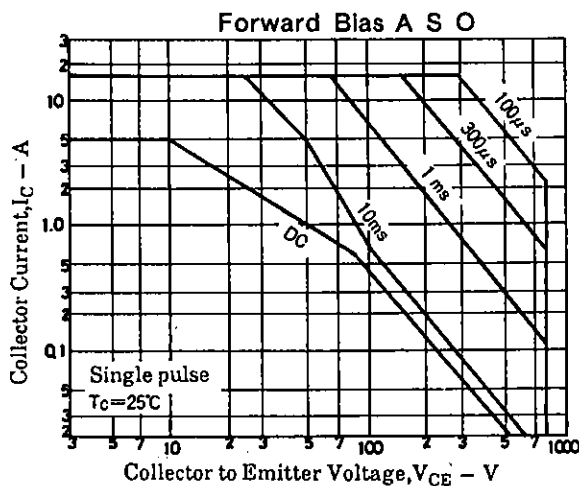
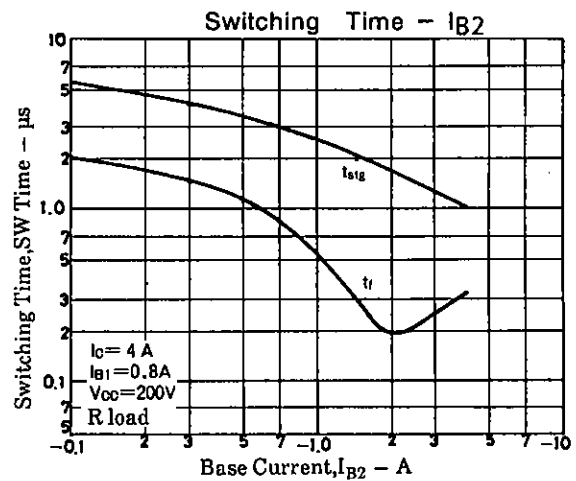
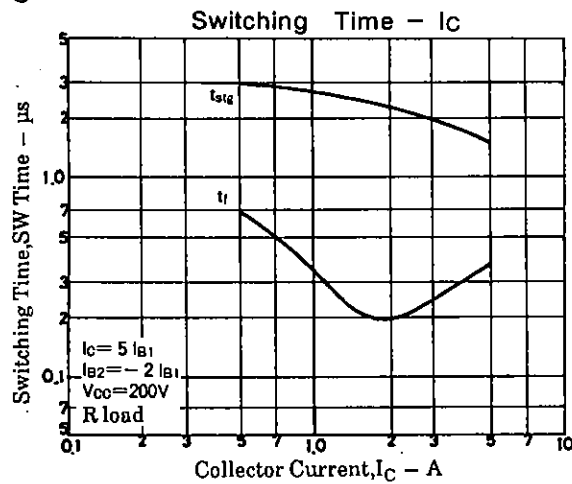
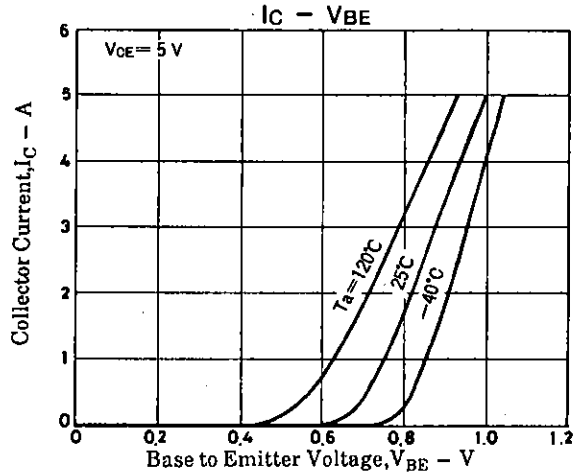
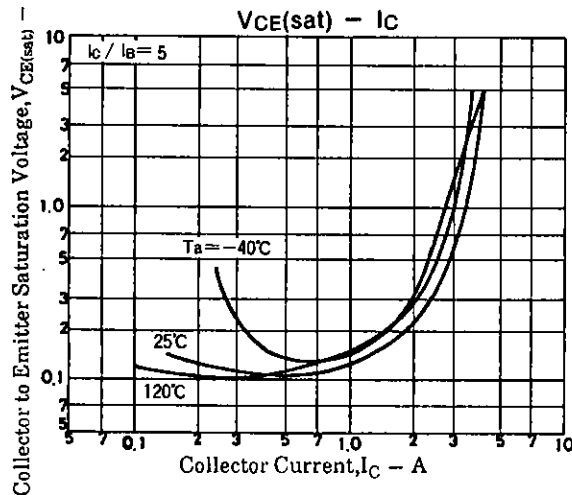
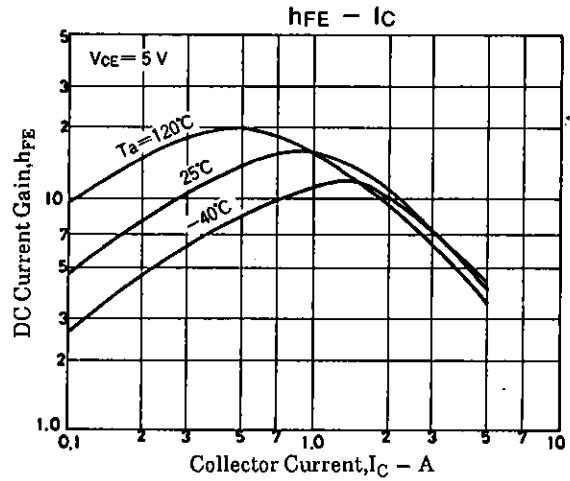
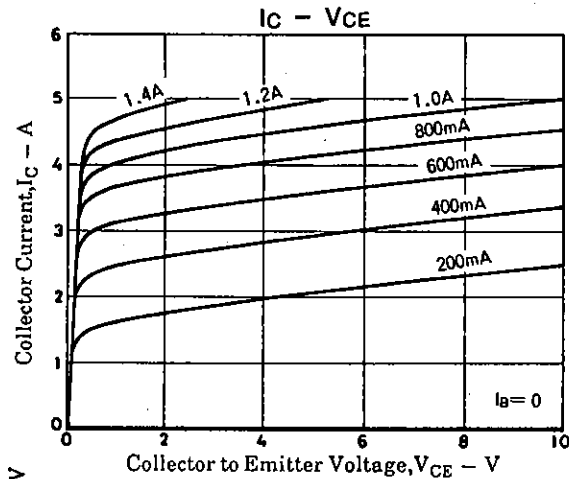
			min	typ	max	unit
Collector Cutoff Current	I_{CES}	$V_{CE} = 1500\text{V}$			1	mA
Collector Cutoff Current	I_{CBO}	$V_{EB} = 800\text{V}$			10	μA
Collector Sustain Voltage	$V_{CEO}(\text{SUS})$	$I_C = 100\text{mA}, I_B = 0$	800			V
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 4\text{V}$	40		130	mA
C-E Saturation Voltage	$V_{CE}(\text{sat})$	$I_C = 4\text{A}, I_B = 1\text{A}$			5	V
B-E Saturation Voltage	$V_{BE}(\text{sat})$	$I_C = 4\text{A}, I_B = 1\text{A}$			1.5	V
DC Current Gain	$h_{FE}(1)$	$V_{CE} = 5\text{V}, I_C = 1\text{A}$	8			
	$h_{FE}(2)$	$V_{CE} = 5\text{V}, I_C = 4\text{A}$	4		6	
Diode Forward Voltage	V_F	$I_{EC} = 5\text{A}$			2.0	V
Storage Time	t_{stg}	$V_{CC} = 200\text{V}, I_C = 4\text{A},$ $I_{B1} = 0.8\text{A}, I_{B2} = -1.6\text{A}$			3.0	μs
Fall Time	t_f				0.3	μs

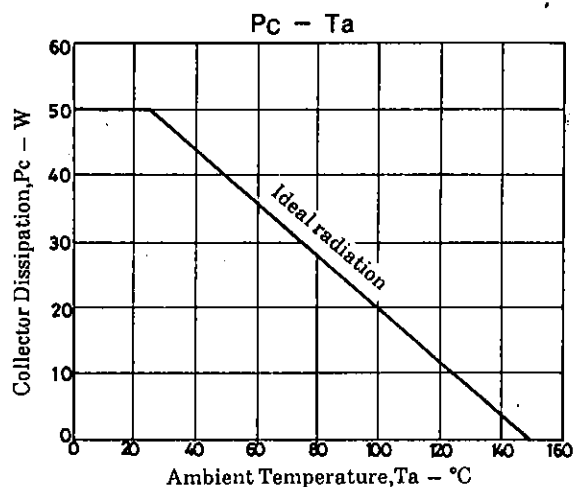
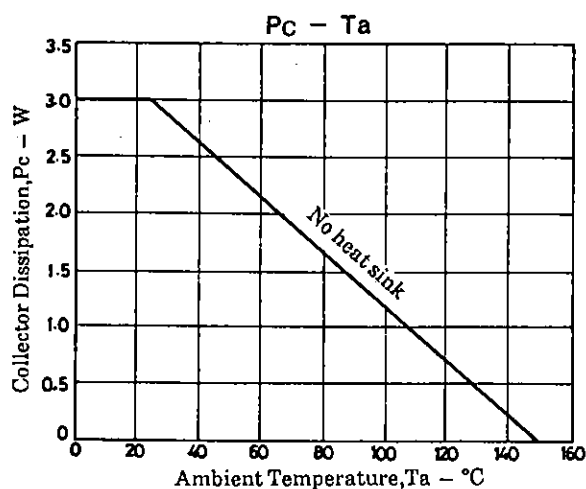
Switching Time Test Circuit**Package Dimensions 2039**

(unit: mm)



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